

February 1999

FDN360P

Single P-Channel PowerTrench™ MOSFET

General Description

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

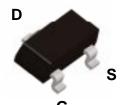
Applications

- DC/DC converter
- Load switch
- Motor drives

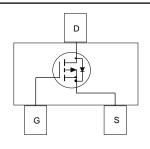
Features

• -2 A, -30 V.
$$R_{DS(on)} = 0.080 \ \Omega \ @ V_{GS} = -10 \ V$$
 $R_{DS(on)} = 0.125 \ \Omega \ @ V_{GS} = -4.5 \ V.$

- Low gate charge (5nC typical).
- · Fast switching speed.
- High performance trench technology for extremely low R_{DS(ON)}.
- High power and current handling capability.







Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		<u>+</u> 20	V
I _D	Drain Current - Continuous	(Note 1a)	-2	Α
	- Pulsed		-20	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T _J , T _{stg}	Operating and Storage Junction Temperatu	re Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R ₀ JC	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity	
360	FDN360P	7"	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30			V
ABVdss ΔTJ	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		20		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-1.8	-3	V
<u>A</u> VGS(th) ΔΤ _J	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-4		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -2 A V _{GS} = -10 V, I _D = -2 A, T _J =125°C V _{GS} = -4.5 V, I _D = -1.5 A		0.060 0.080 0.095	0.080 0.136 0.125	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = -10 V, V _{DS} = -5 V	-20			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_{D} = -2 \text{ A}$		5.5		S
Dynamic	Characteristics	•				
C _{iss}	Input Capacitance					pF
C _{oss}	Output Capacitance	f = 1.0 MHz		140		pF
C _{rss}	Reverse Transfer Capacitance			60		pF
	ng Characteristics (Note 2)	-			I	
SWILCIIII	Turn-On Delay Time	$V_{DD} = -15 \text{ V}, I_D = -1 \text{ A},$		9	18	ns
t _{d(on)}	rain on bolay rimo			8	16	ns
	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$		0	10	
$t_{d(on)}$ t_r $t_{d(off)}$	•	$V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$		18	29	ns
t _r	Turn-On Rise Time	V_{GS} = -10 V, R_{GEN} = 6 Ω		_	_	ns ns
tr	Turn-On Rise Time Turn-Off Delay Time	$V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$ $V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A},$		18	29	
t_r $t_{d(off)}$ t_f Q_g	Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time			18	29 12	ns
t _r t _{d(off)} t _f	Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge	V _{DS} = -15 V, I _D = -2 A,		18 6 5	29 12	ns nC
$\begin{array}{c} t_r \\ t_{d(off)} \\ t_f \\ Q_g \\ Q_{gs} \\ Q_{gd} \end{array}$	Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A},$ $V_{GS} = -10 \text{ V},$		18 6 5 1.7	29 12	ns nC nC
$\begin{array}{c} t_r \\ t_{d(off)} \\ t_f \\ Q_g \\ Q_{gs} \\ Q_{gd} \end{array}$	Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge	V _{DS} = -15 V, I _D = -2 A, V _{GS} = -10 V,		18 6 5 1.7	29 12	ns nC nC

Notes

 R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² Pad of 2 oz. Cu.



b) 270°C/W when mounted on a 0.001 in² pad of 2 oz. Cu.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$

Typical Characteristics

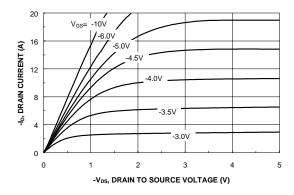


Figure 1. On-Region Characteristics.

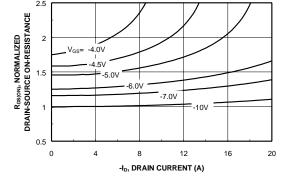


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

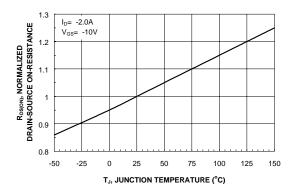


Figure 3. On-Resistance Variation with Temperature.

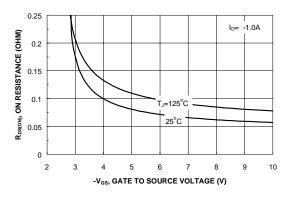


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

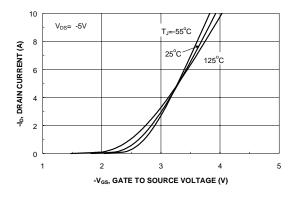


Figure 5. Transfer Characteristics.

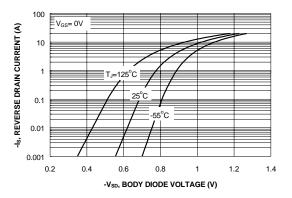
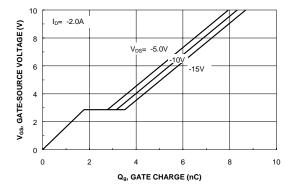


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



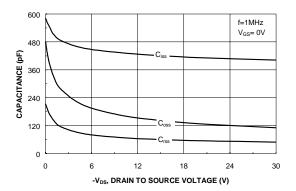
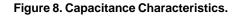
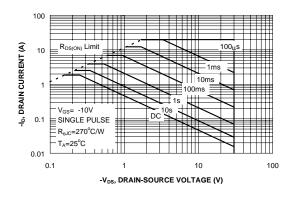


Figure 7. Gate Charge Characteristics.





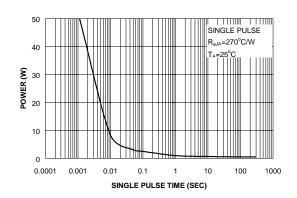


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

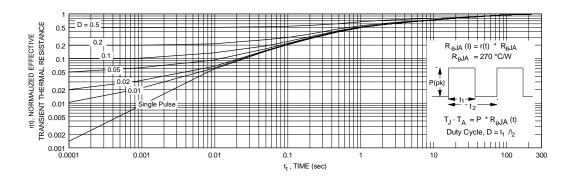
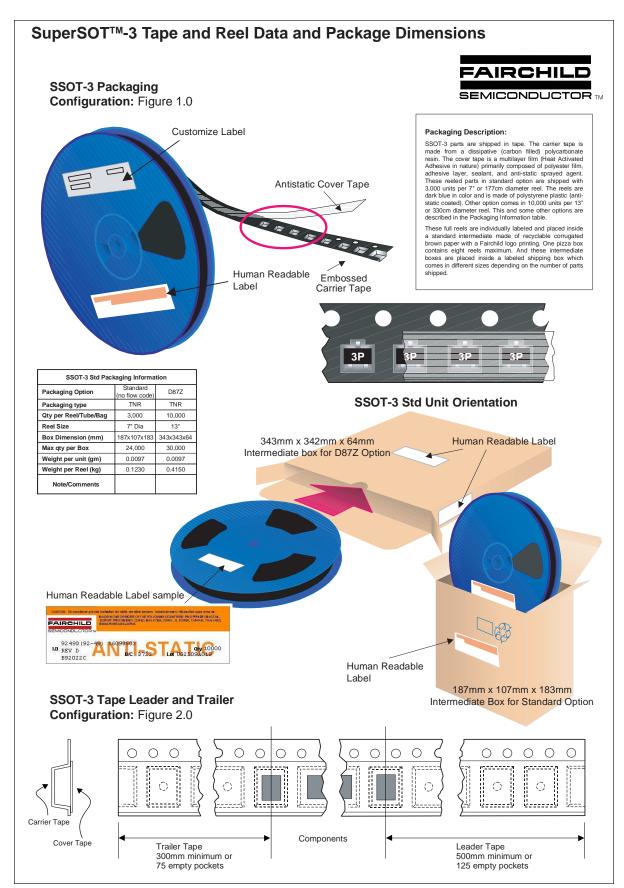
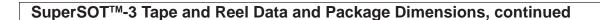


Figure 11. Transient Thermal Response Curve.

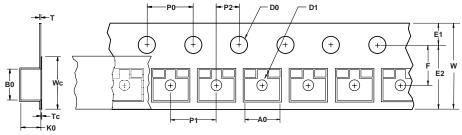
Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.





SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



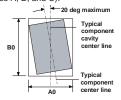


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

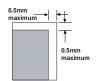
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



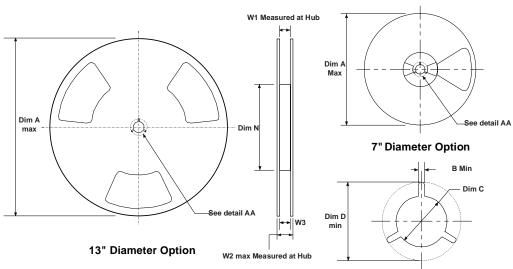
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

DETAIL AA

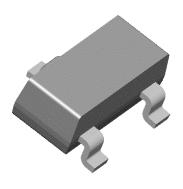
SSOT-3 Reel Configuration: Figure 4.0

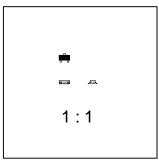


	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

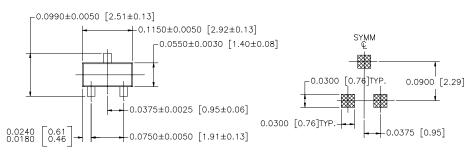
SuperSOT™-3 (FS PKG Code 32)



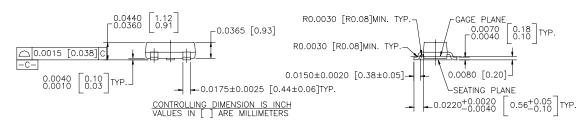


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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Datasheet Identification	Product Status	Definition
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